

AMENDMENT

Please amend claim 18 to read as follows:

18. (Amended) A process for fabrication of a semiconductor device, the device including a floating gate FLASH structure comprising an ONO structure, comprising forming the ONO structure by:

- providing a semiconductor substrate having a floating gate electrode;
- forming a bottom oxide layer overlying the floating gate electrode by in-situ steam generation oxidation of a portion of a surface of the floating gate electrode;
- depositing a silicon nitride layer overlying the bottom oxide layer; and
- forming a top oxide layer overlying the silicon nitride layer by in-situ steam generation oxidation of a portion of the silicon nitride layer.